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INTERNATIONAL STANDARD

Semiconductor devices -
Part 2: Discrete devices - Rectifier diodes

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Semiconductor devices - Part 2: Discrete devices - Rectifier diodes

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IEC 60747-2 has been prepared by subcommittee 47E: Discrete semiconductor devices, of IEC technical committee 47: Semiconductor devices. It is an International Standard.

This fourth edition cancels and replaces the third edition published in 2016. This edition constitutes a technical revision.

This edition includes the following significant technical changes with respect to the previous edition:

a) the terms and definitions for partial thermal resistance junction-to-case have been added;
b) Clauses 3, 4, 5, 6 and 7 have been amended with some deletions of information no longer in use and with some necessary additions.

The text of this International Standard is based on the following documents:

Draft	Report on voting
47E/861/FDIS	47E/869/RVD

Full information on the voting for its approval can be found in the report on voting indicated in the above table.

The language used for the development of this International Standard is English.

This document was drafted in accordance with ISO/IEC Directives, Part 2, and developed in accordance with ISO/IEC Directives, Part 1 and ISO/IEC Directives, IEC Supplement, available at www.iec.ch/members_experts/refdocs. The main document types developed by IEC are described in greater detail at www.iec.ch/publications.

This International Standard is to be used in conjunction with IEC 60747-1:2006 and its Amendment 1:2010.

A list of all parts in the IEC 60747 series, published under the general title *Semiconductor devices*, can be found on the IEC website.

The committee has decided that the contents of this document will remain unchanged until the stability date indicated on the IEC website under webstore.iec.ch in the data related to the specific document. At this date, the document will be

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